

interlayer insulating films formed on said main surface;
conductive interconnections provided in a plurality of layers separated by said
interlayer insulating films; and
conductive dummy interconnections provided in the same layers as said
interconnections in two or more layers included in said plurality of layers,
wherein at least one of said dummy interconnections has repetitive protrusions and
recesses along its elongate direction in a section taken along said main surface.

11. (Amended) A semiconductor device comprising:

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a semiconductor substrate having a main surface along which a semiconductor
element is formed;

interlayer insulating films formed on said main surface;
conductive interconnections provided in a plurality of layers separated by said
interlayer insulating films; and
conductive dummy interconnections provided in the same layers as said
interconnections in two or more layers included in said plurality of layers,
wherein at least one of said dummy interconnections has repetitive protrusions and
recesses along its elongate direction in a section taken along a plane perpendicular to said
main surface.

Please add the following new claims:

21. The semiconductor device according to claim 10, wherein potentials
corresponding to each of said lower-potential power-supply line or a higher-potential power-
supply line are connected to said dummy conductive plug

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22. The semiconductor device according to claim 10, comprising:

a conductive dummy plug selectively buried in said interlayer insulating films to
connect said dummy interconnections between said two or more layers and connected